


Features

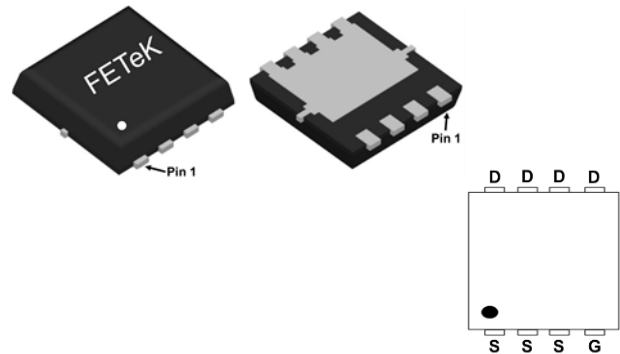
- Advanced Trench MOS Technology
- 100% EAS Guaranteed
- Green Device Available

Product Summary

BVDSS	RDSON	ID
-150V	780mΩ	-2A

Applications

- Load Switch.
- Power Management.
- LED Backlighting.
- Networking Application.

PRPAK3X3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-2	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-1.5	A
I_{DM}	Pulsed Drain Current ²	-8	A
EAS	Single Pulse Avalanche Energy ³	12.5	mJ
I_{AS}	Avalanche Current	5	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	7.8	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	16	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-150	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-1A$	---	650	780	m Ω
		$V_{GS}=-6V, I_D=-0.5A$	---	700	980	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-2.0	-3.0	-4.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-120V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=-120V, V_{GS}=0V, T_J=85^\circ\text{C}$	---	---	30	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	5	12	20	Ω
Q_g	Total Gate Charge	$V_{DS}=-75V, V_{GS}=-10V, I_D=-1A$	6.5	10.8	15.2	nC
Q_{gs}	Gate-Source Charge		1.6	3.1	4.7	
Q_{gd}	Gate-Drain Charge		1.1	2.2	3.3	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-30V, V_{GS}=-10V, R_G=6\Omega, I_D=-1A$	---	21	32	ns
T_r	Rise Time		---	16	24	
$T_{d(off)}$	Turn-Off Delay Time		---	40	60	
T_f	Fall Time		---	18	27	
C_{iss}	Input Capacitance	$V_{DS}=-75V, V_{GS}=0V, f=1\text{MHz}$	424	706	988	pF
C_{oss}	Output Capacitance		12	23	35	
C_{rss}	Reverse Transfer Capacitance		7	13	20	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-1	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-50V, V_{GS}=-10V, L=1\text{mH}, I_{AS}=-5A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

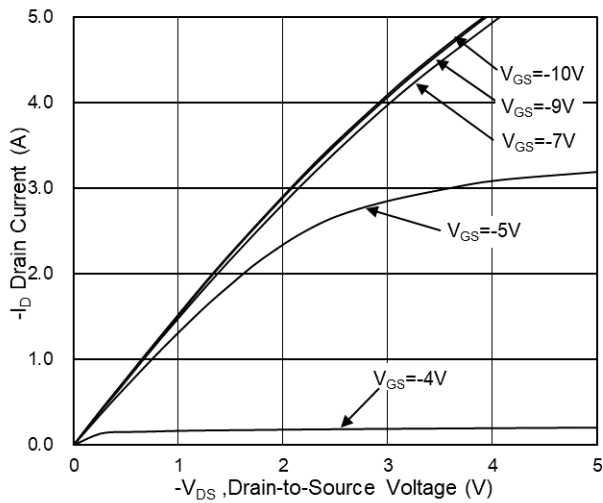


Fig.1 Typical Output Characteristics

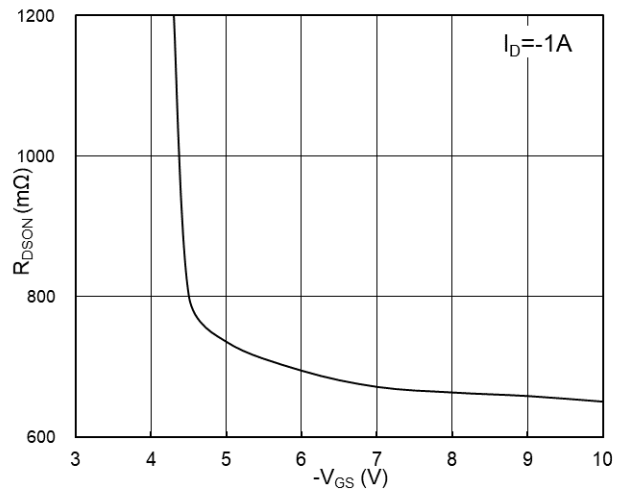


Fig.2 On-Resistance vs G-S Voltage

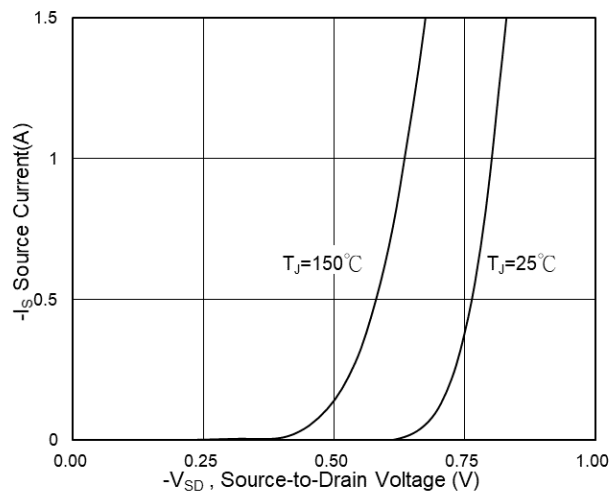


Fig.3 Source Drain Forward Characteristics

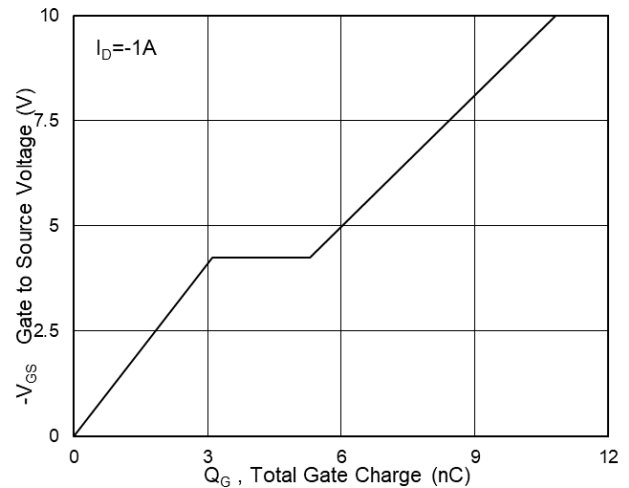


Fig.4 Gate-Charge Characteristics

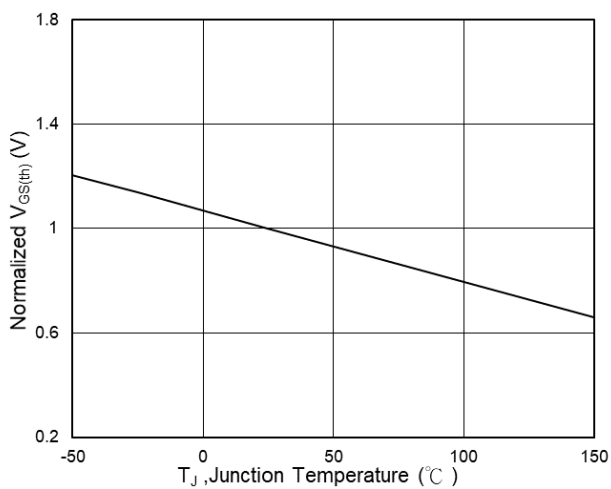


Fig.5 Normalized $V_{GS(th)}$ vs T_J

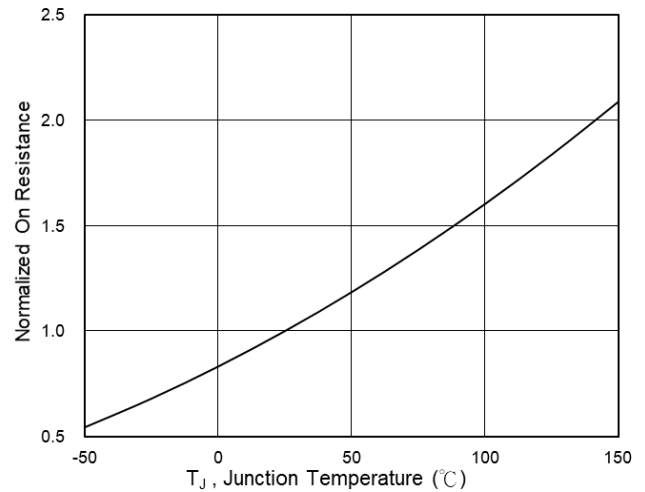


Fig.6 Normalized $R_{DS(ON)}$ vs T_J

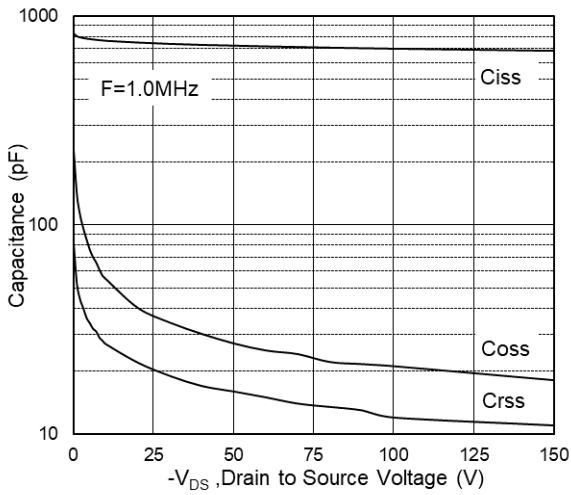


Fig.7 Capacitance

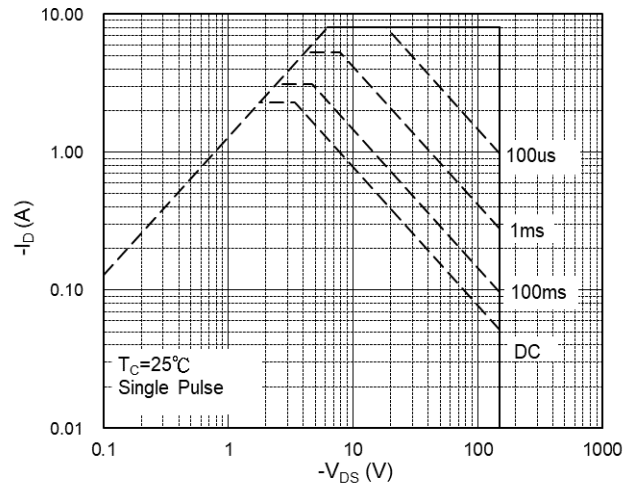


Fig.8 Safe Operating Area

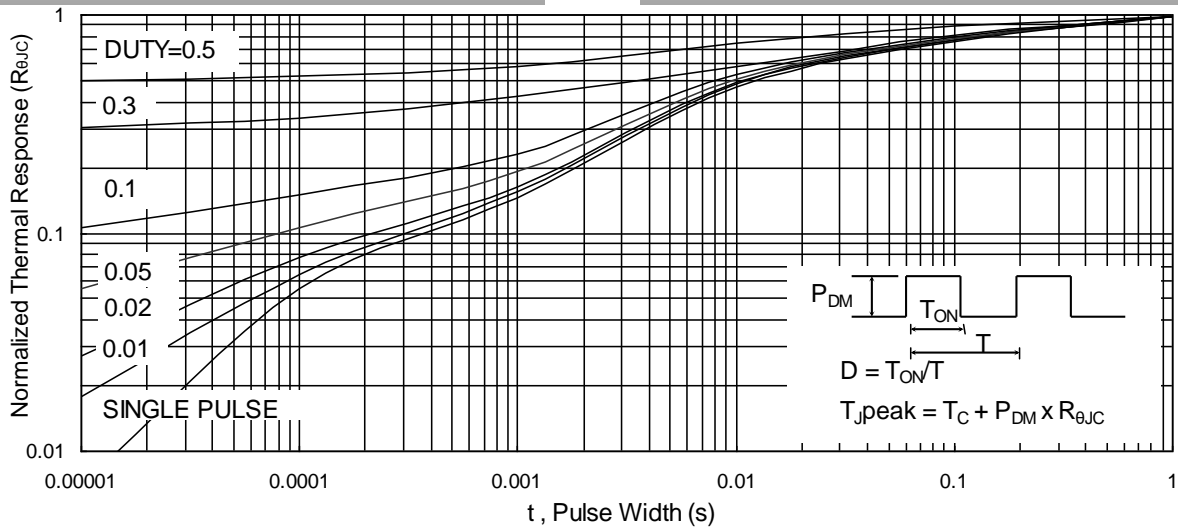


Fig.9 Normalized Maximum Transient Thermal Impedance

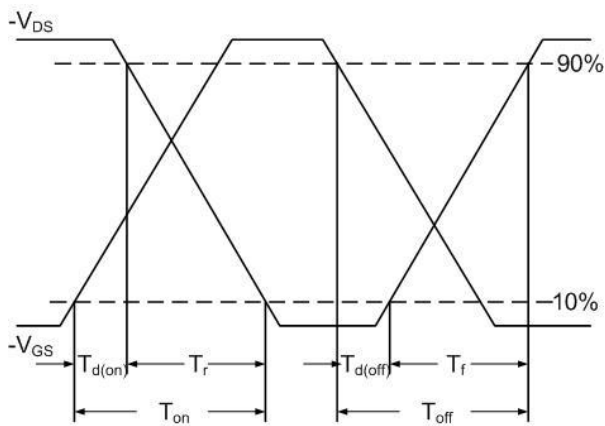


Fig.10 Switching Time Waveform

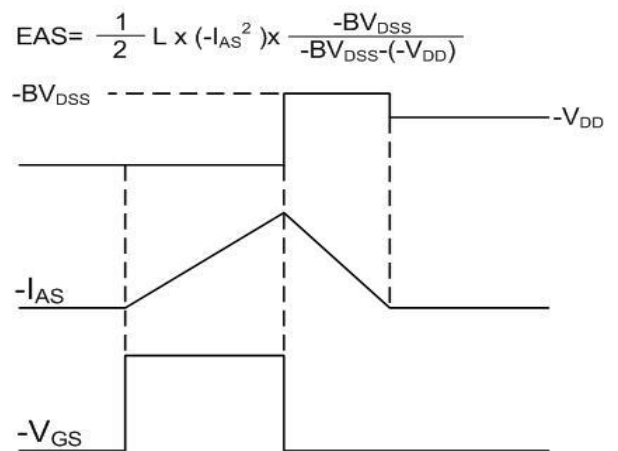
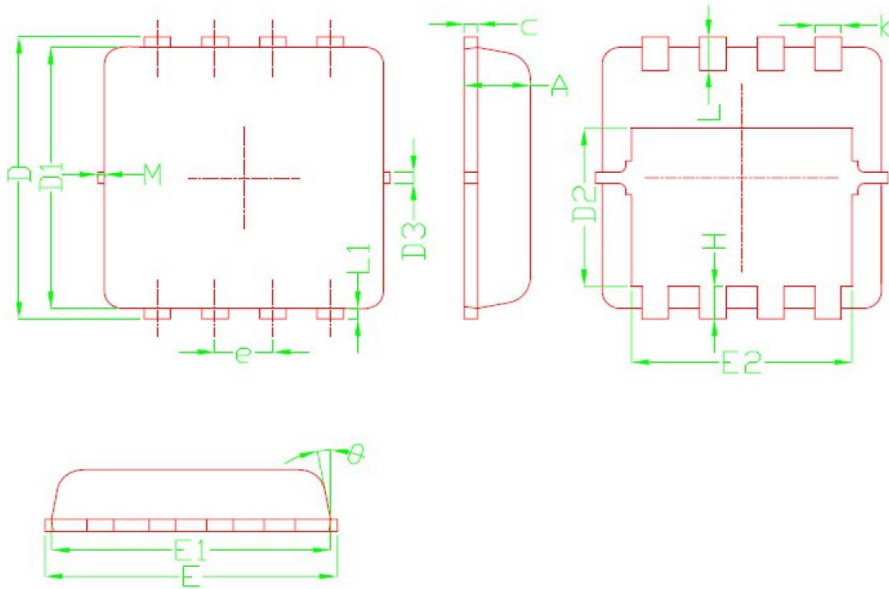


Fig.11 Unclamped Inductive Waveform

PRPAK3x3-8L Package Outline



Symbols	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.70	0.85	0.027	0.034
b	0.20	0.40	0.007	0.016
c	0.10	0.25	0.004	0.010
D	3.15	3.45	0.124	0.136
D1	2.90	3.20	0.114	0.126
D2	1.54	1.98	0.060	0.080
D3	0.10	0.30	0.004	0.012
E	3.15	3.45	0.124	0.136
E1	3.00	3.25	0.118	0.128
E2	2.29	2.65	0.090	0.104
e	0.65 BSC		0.025 BSC	
H	0.28	0.65	0.011	0.026
θ	0°	14°	0°	14°
L	0.30	0.50	0.012	0.020
L1	0.13		0.005	
M	---	0.15	---	0.006

